Abstracts

An 11 W Ku-Band Heterostructure FET with WSi/Au T-Shaped Gate

J. Udomoto, S. Chaki, M. Komaru, T. Kunii, Y. Kohno, S. Goto, K. Gotoh, A. Inoue, N. Tanino, T. Takagi and O. Ishihara. "An 11 W Ku-Band Heterostructure FET with WSi/Au T-Shaped Gate." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 339-342.

We developed a Heterostructure FET (HFET) with a high output power and a high power-added efficiency (PAE) at Ku-band. 8 W and 11.2 W output powers were obtained with power-added efficiencies of 48% and 41% and linear gains of 9 dB and 8.6 dB at 12 GHz, respectively. This is the highest power and efficiency ever reported which is achieved by a single FET chip at this frequency.

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